

MMBT5401

MMBT5401 TRANSISTOR (PNP)

FEATURES

Complimentary to MMBT5551

MARKING:2L

MAXIMUM RATINGS (TA=25°C unless otherwise noted)



| Symbol (符号) | Parameter (参数名称) | Value (额定值) | Units (单位) |
|----------------|---------------------------------------|----------------|---------------|
| VCBO | Collector-Base Voltage (集电极-基极电压) | -160 | V |
| VCEO | Collector-Emitter Voltage (集电极-发射极电压) | -150 | V |
| VEBO | Emitter-Base Voltage (发射极-基极电压) | -5 | V |
| IC | Collector Current -Continuous (集电极电流) | -0.6 | A |
| PC | Collector Power Dissipation (耗散功率) | 0.3 | W |
| Tj | Junction Temperature (结温) | 150 | °C |
| Tstg | Storage Temperature (储存温度) | -55-150 | °C |

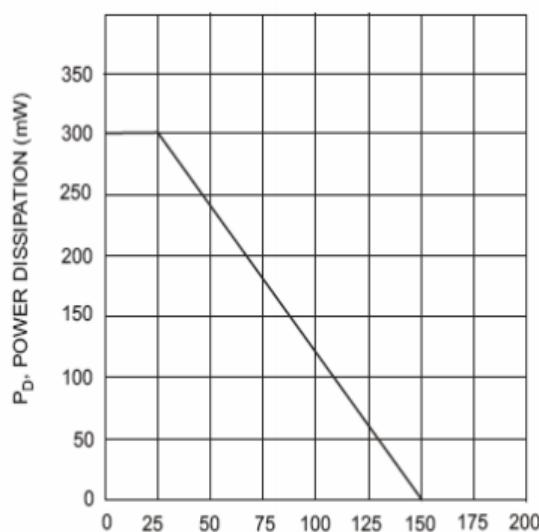
ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter (参数名称) | Symbol (符号) | Test conditions (测试条件) | MIN (最小值) | TYP (典型值) | MAX (最大值) | UNIT (单位) |
|---|----------------|---------------------------|--------------|--------------|--------------|--------------|
| Collector-base breakdown voltage 集电极-基极击穿电压 | V(BR)CBO | IC= -100μA, IE=0 | -160 | | | V |
| Collector-emitter breakdown voltage 集电极-发射极击穿电压 | V(BR)CEO | IC= -1mA, IB=0 | -150 | | | V |
| Emitter-base breakdown voltage 发射极-基极击穿电压 | V(BR)EBO | IE=-100μA, IC=0 | -5 | | | V |
| Collector cut-off current 集电极-基极截止电流 | ICBO | VCB=-120 V , IE=0 | | | -1 | μ A |
| Collector cut-off current 集电极-发射极截止电流 | ICEO | VCE=-120V , IB=0 | | | -10 | μ A |
| Emitter cut-off current 发射极-基极截止电流 | IEBO | VEB=-5V , IC=0 | | | -1 | μ A |
| DC current gain 直流电流增益 | hFE | VCE=-5V, IC= -10mA | 100 | | 400 | |
| Collector-emitter saturation voltage 集电极-发射极饱和压降 | VCE(sat) | IC=-50mA, IB= -5mA | | | -0.5 | V |
| Base-emitter saturation voltage 发射极-基极饱和压降 | VBE(sat) | IC=-50mA, IB= -5mA | | | -1 | V |

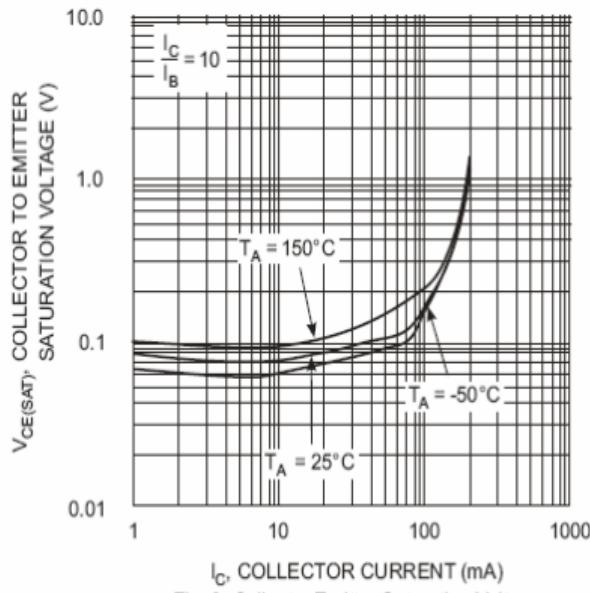
CLASSIFICATION OF hFE

| | | | | |
|-------|---------|---------|---------|--|
| Range | 100-200 | 200-300 | 300-400 | |
|-------|---------|---------|---------|--|

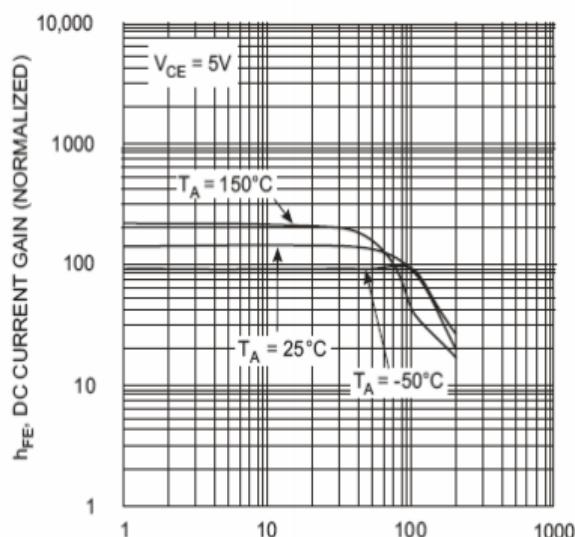
Typical Characteristics



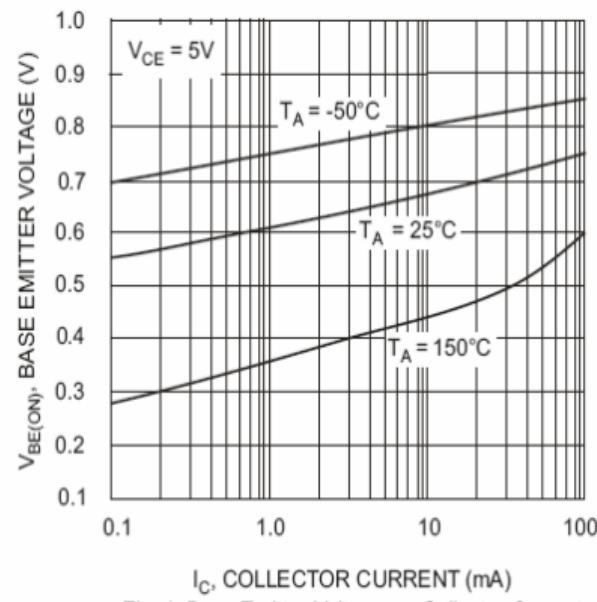
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs
Ambient Temperature



I_C , COLLECTOR CURRENT (mA)
Fig. 2, Collector Emitter Saturation Voltage
vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 3, DC Current Gain vs. Collector Current



I_C , COLLECTOR CURRENT (mA)
Fig. 4, Base Emitter Voltage vs. Collector Current

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